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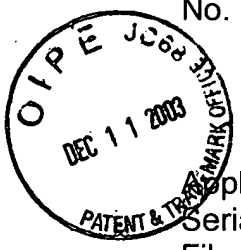


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster et al.
Serial No. 10/685,251
Filed October 14, 2003

For LOW DEFECT DENSITY, SELF-INTERSTITIAL DOMINATED SILICON

December 11, 2003

COMMISSIONER FOR PATENTS
P.O. BOX 1450
ALEXANDRIA, VIRGINIA 22313-1450

SIR:

INFORMATION DISCLOSURE STATEMENT

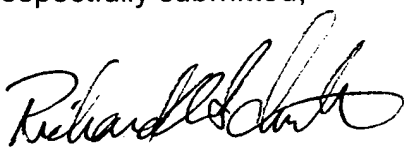
This Information Disclosure Statement is being submitted pursuant to 37 C.F.R. §1.97(b) in that applicants believe that it is being filed prior to the mailing date of the first Office action on the merits. Accordingly, neither a statement nor fee under 37 C.F.R. §1.97(c) or (d) is required. However, if an Office action was issued prior to the date of mailing of this Information Disclosure Statement, the Commissioner is hereby authorized to charge any required fees regarding this Information Disclosure Statement to Deposit Account No. 19-1345.

In accordance with 37 C.F.R. 1.97 and 1.98 and MPEP 609, and in compliance with the duty of disclosure set forth in 37 C.F.R. 1.56, applicants submit the attached PTO/SB/08A for consideration by the Patent and Trademark Office in the above-entitled application and to be made of record therein. In accordance with the Pre-OG notice of July 11, 2003 partially waiving the requirements of 37 C.F.R. 1.98(a)(2)(i), copies of the U.S. patent documents are not supplied.

Regarding the remaining non-U.S. references, please note that numbers 21-23, 25-31, 33-37, 42-76, 78-101, 103-109, and 111-123 listed on the attached PTO/SB/08A have been made of record in parent application Serial No. 10/135,597 filed April 30, 2002, now U.S. Patent No. 6,632,278 B2 and, therefore, in accordance with MPEP 609, copies are not being provided at this time.

Please note that Applicants make no representation as to the accuracy or completeness of the translations of the abstracts submitted herewith.

Respectfully submitted,



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PTO/SB/08A	Complete if Known	
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(use as many sheets as necessary)	Confirmation Number	Unknown
	First Named Inventor	Robert J. Falster et al.
	Group Art Unit	Unknown
	Examiner Name	Unknown
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Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	U.S. Patent Document Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
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				Group Art Unit	Unknown
				Examiner Name	Unknown
Sheet	8	of	9	Attorney Docket No.	MEMC 96-0055(2101.3)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/685,251
				Filing Date	October 14, 2003
(use as many sheets as necessary)				Confirmation Number	Unknown
				First Named Inventor	Robert J. Falster et al.
				Group Art Unit	Unknown
				Examiner Name	Unknown
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